

/ Descriptions

KF \$,) E GE Silicon NPN transistor in a TO-252 Plastic Package.

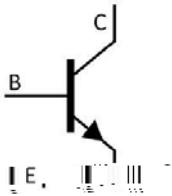
/ Features

) J9- +08;
Complementary pair with 2SB649AD.

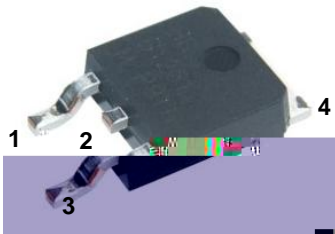
/ Applications

Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	B	C	D
h _{FE} Range	60 120	100 200	160 320

2SD669AD

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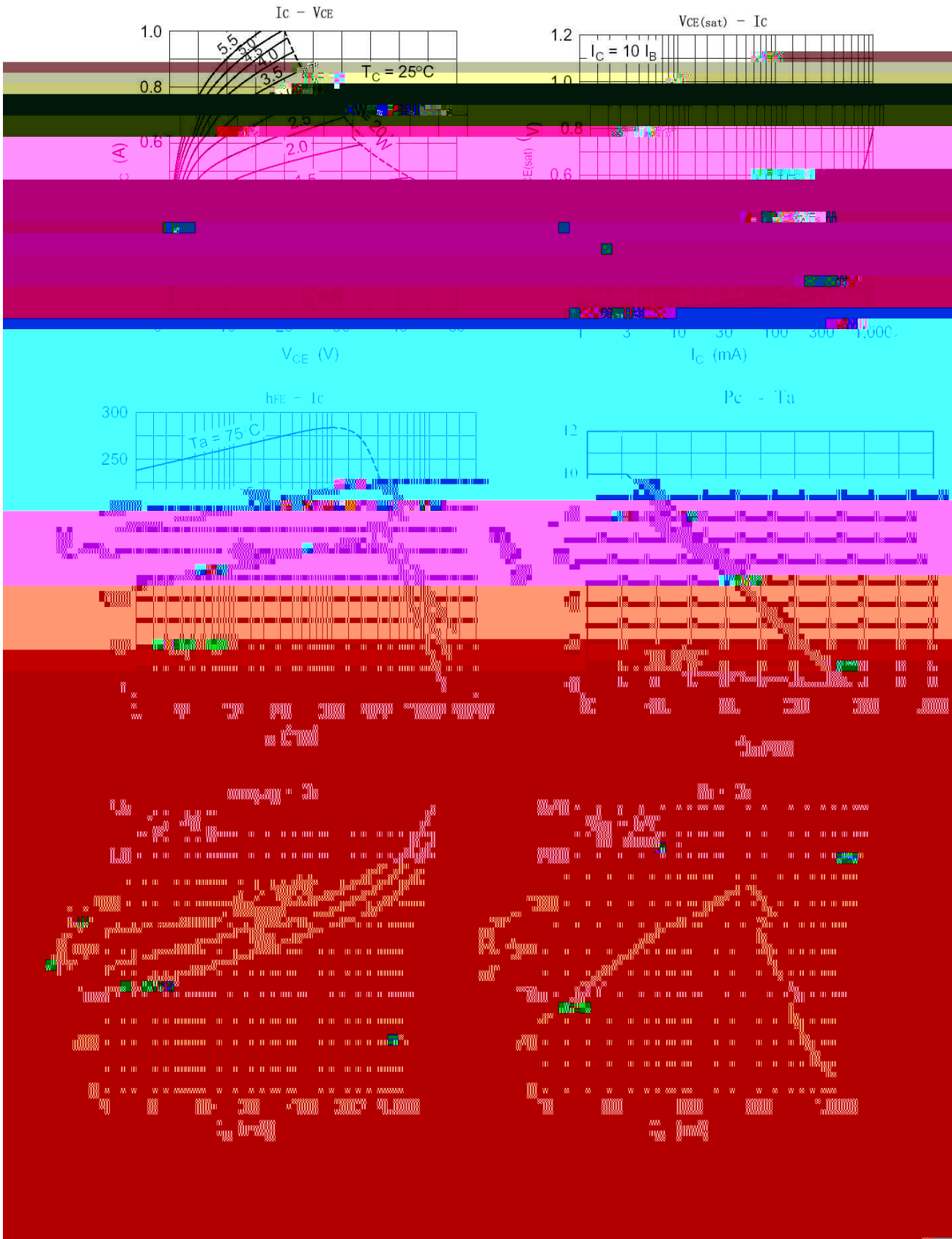


DATA SHEET

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	180	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.5	A
Collector Current – Continuous(Pulse)	I_{CP}	3.0	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ\text{C})$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=1.0\text{mA}$ $I_E=0$	180			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10\text{mA}$ $R_{BE}=\infty$	160			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_B=10\text{mA}$				V

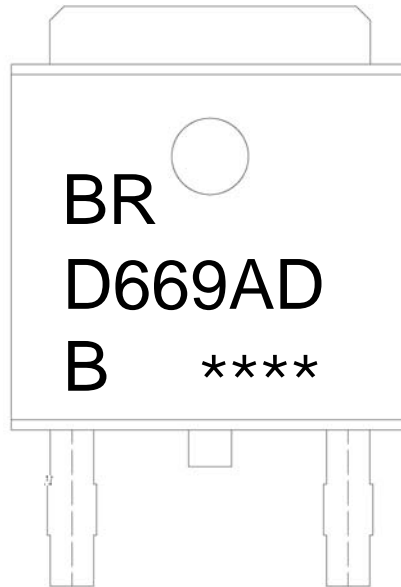
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

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91 h_{FE}

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Note:

BR: Company Code

D669AD: Product Type.

B: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

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